



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

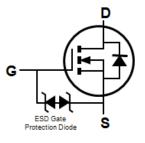
- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 63
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)



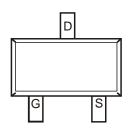












Top View

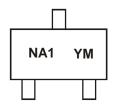
Ordering Information (Note 5)

Part Number	Qualification	Case	Packaging
DMG1012T-7	Commercial	SOT523	3000/Tape & Reel
DMG1012T-13	Commercial	SOT523	10000/Tape & Reel
DMG1012TQ-7	Automotive	SOT523	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
- The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum V_{GSS} rating (given on page 2) can be applied.

Marking Information



NA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2009		2018	2019	2020	20:	21 2	2022	2023	2024	2025	2026
Code	W		F	G	Н	I		J	K	L	М	N
Month	lon	Feb	Mor	Anr	Max	lum	lul	A	Son	Oct	Nov	Doo
MOHUI	Jan	reb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	NOV	Dec

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characterist	ic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	20	V	
Gate-Source Voltage		V _{GSS}	±6	V	
Continuous Drain Current (Note 7)	Steady State	$T_A = +25$ °C $T_A = +85$ °C	I _D	0.63 0.45	А
Pulsed Drain Current			I _{DM}	3	A

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 7)	P_{D}	0.28	W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{ heta JA}$	452	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

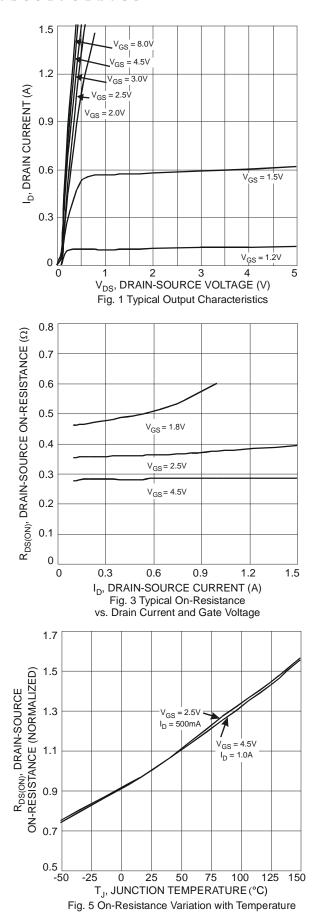
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	100	nA	$V_{DS} = 20V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	_	_	±1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
			0.3	0.4		$V_{GS} = 4.5V, I_D = 600mA$		
Static Drain-Source On-Resistance	R _{DS(ON)}	_	0.4	0.5	Ω	$V_{GS} = 2.5V, I_D = 500mA$		
			0.5	0.7		$V_{GS} = 1.8V, I_D = 350mA$		
Forward Transfer Admittance	Y _{fs}	_	1.4	_	S	$V_{DS} = 10V, I_D = 400mA$		
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	C _{iss}	_	60.67	_	pF	101/11/		
Output Capacitance	Coss	_	9.68	_	pF	$V_{DS} = 16V, V_{GS} = 0V,$ - f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	_	5.37	_	pF	1 = 1.000112		
Total Gate Charge	Qg	_	736.6	_	рC	4.51/.1/		
Gate-Source Charge	Q _{qs}	_	93.6	_	рС	$V_{GS} = 4.5V, V_{DS} = 10V,$		
Gate-Drain Charge	Q _{gd}	_	116.6	_	рС	$I_D = 250 \text{mA}$		
Turn-On Delay Time	t _{D(ON)}	_	5.1	_	ns	101/11/		
Turn-On Rise Time	t _R	_	7.4	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$		
Turn-Off Delay Time	t _{D(OFF)}	_	26.7	_	ns	$R_L = 47\Omega$, $R_G = 10\Omega$,		
Turn-Off Fall Time	t _F	_	12.3	_	ns	$I_D = 200 \text{mA}$		

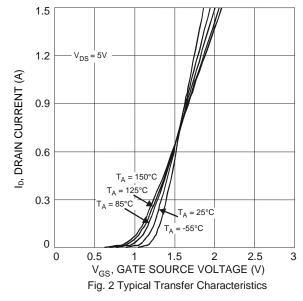
Notes:

- 7. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

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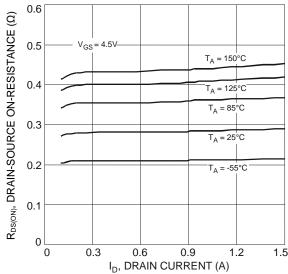


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

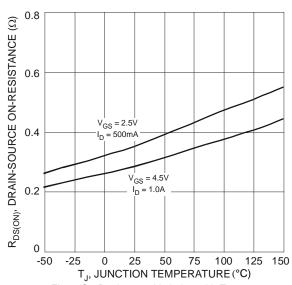


Fig. 6 On-Resistance Variation with Temperature



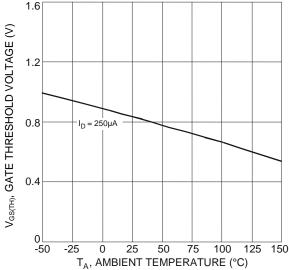
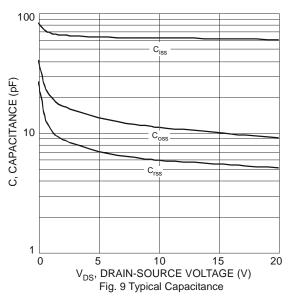
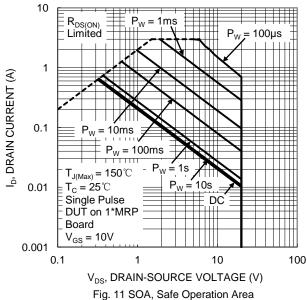
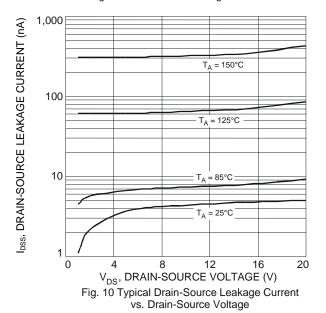


Fig. 7 Gate Threshold Variation vs. Ambient Temperature









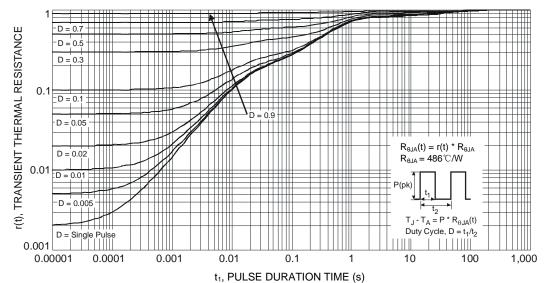


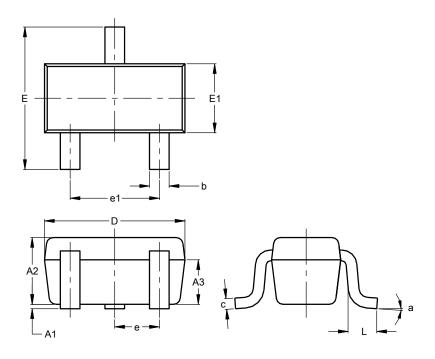
Fig. 12 Transient Thermal Response



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

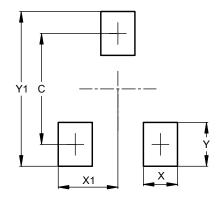


SOT523								
Dim	Min	Max	Тур					
A1	0.00	0.10	0.05					
A2	0.60	0.80	0.75					
A3	0.45	0.65	0.50					
b	0.15	0.30	0.22					
С	0.10	0.20	0.12					
D	1.50	1.70	1.60					
Е	1.45	1.75	1.60					
E1	0.75	0.85	0.80					
е	e 0.50 BSC							
e1	0.90	1.10	1.00					
L	0.20	0.40	0.33					
а	0°		8°					
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)			
С	1.29			
Х	0.40			
X1	0.70			
Y	0.51			
V1	1.80			



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